

Features

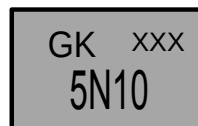
100V,6A , $R_{DS(ON)}=95m\Omega@V_{GS}=10V$

Improved dv/dt capability

Fast switching

Green Device Available

V_{DSS} 100 V
 I_D 5 A
 $R_{DS(ON)}$ 95 m Ω



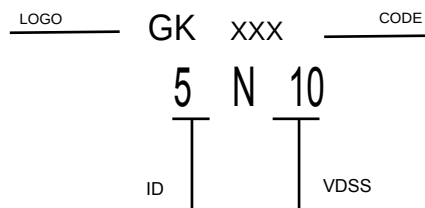
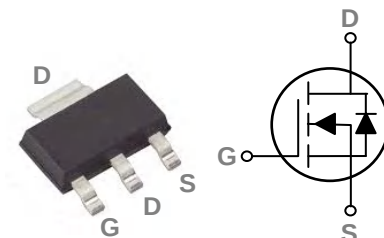
Application

Networking

Load Switch

LED applications

SOT223 Pin Configuration



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Maximum ratings ($T_a=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current – Continuous ($T_A=25^\circ\text{C}$)	5	A
	Drain Current Continuous ($T = 70^\circ\text{C}$)	2.9	A
I_{DM}	Drain Current – Pulsed ¹	18	A
P_D	Power Dissipation ($T = 25^\circ\text{C}$)	5.2	W
	Power Dissipation Derate above 25°C	0.042	W/ $^\circ\text{C}$
T_{STG}	Storage Temperature Range	-50 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-50 to 125	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient	---	85	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction to Case	---	24	$^\circ\text{C/W}$

Electrical Characteristics $T_A=25^{\circ}\text{C}$ unless otherwise specified

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	100	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.09	---	$V/^{\circ}\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=100V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
		$V_{DS}=80V$, $V_{GS}=0V$, $T_J=125^{\circ}\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=4A$	---	95	120	$m\Omega$
		$V_{GS}=4.5V$, $I_D=2A$	---	100	145	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1.0	1.6	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-5	---	$mV/^{\circ}\text{C}$
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=2A$	---	8.7	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{2, 3}	$V_{DS}=50V$, $V_{GS}=10V$, $I_D=2A$	---	20	---	nC
Q_{gs}	Gate-Source Charge ^{2, 3}		---	3.2	---	
Q_{gd}	Gate-Drain Charge ^{2, 3}		---	3.6	---	
$T_{d(on)}$	Turn-On Delay Time ^{2, 3}	$V_{DD}=50V$, $V_{GS}=10V$, $R_G=3.3\Omega$ $I_D=1A$	---	18	---	ns
T_r	Rise Time ^{2, 3}		---	4	---	
$T_{d(off)}$	Turn-Off Delay Time ^{2, 3}		---	40	---	
T_f	Fall Time ^{2, 3}		---	3	---	
C_{iss}	Input Capacitance	$V_{DS}=25V$, $V_{GS}=0V$, $F=1\text{MHz}$	---	1100	---	pF
C_{oss}	Output Capacitance		---	60	---	
C_{rss}	Reverse Transfer Capacitance		---	35	---	

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	6.0	A
I_{SM}	Pulsed Source Current		---	---	12	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_S=1A$, $T_J=25^{\circ}\text{C}$	---	---	1.3	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. $V_{DD}=50V$, $V_{GS}=10V$, $L=0.1\text{mH}$, $I_{AS}=23A$, $R_G=25\Omega$, Starting $T_J=25^{\circ}\text{C}$
3. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
4. Essentially independent of operating temperature.

RATING AND CHARACTERISTIC CURVES

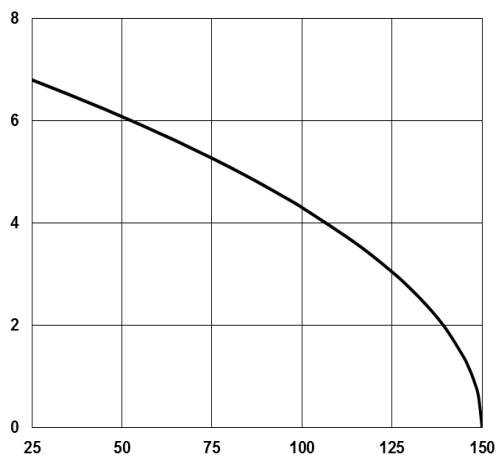


Fig.1 Continuous Drain Current vs. T_c

Normalized On Resistance ($m\Omega$)

T_J , Junction Temperature (°C)

Fig.2 Normalized $R_{DS(on)}$ vs. T_J

Normalized Gate Threshold Voltage (V)

T_J , Junction Temperature (°C)

Fig.3 Normalized V_{th} vs. T_J

V_{GS} , Gate to Source Voltage (V)

Q_g , Gate Charge (nC)

Fig.4 Gate Charge Waveform

Normalized Thermal Response ($R_{\theta JA}$)

Square Wave Pulse Duration (s)

Fig.5 Normalized Transient Impedance

I_D , Continuous Drain Current (A)

V_{DS} , Drain to Source Voltage (V)

Fig.6 Maximum Safe Operation Area

RATING AND CHARACTERISTIC CURVES

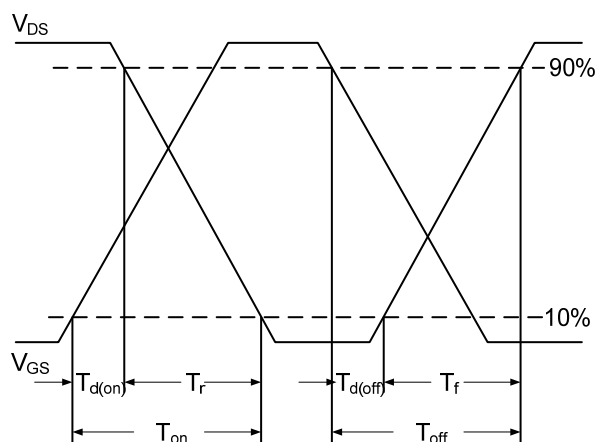


Fig.7 Switching Time Waveform

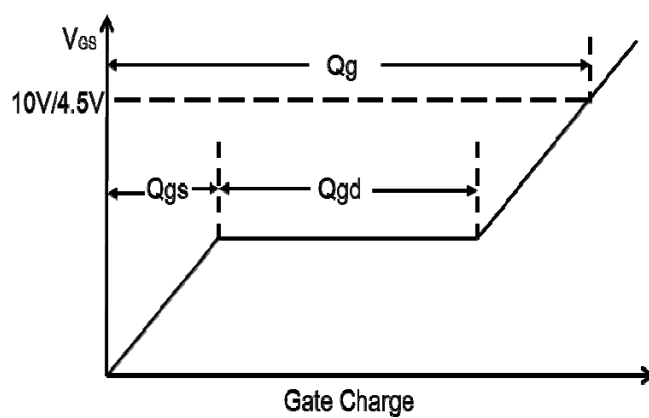
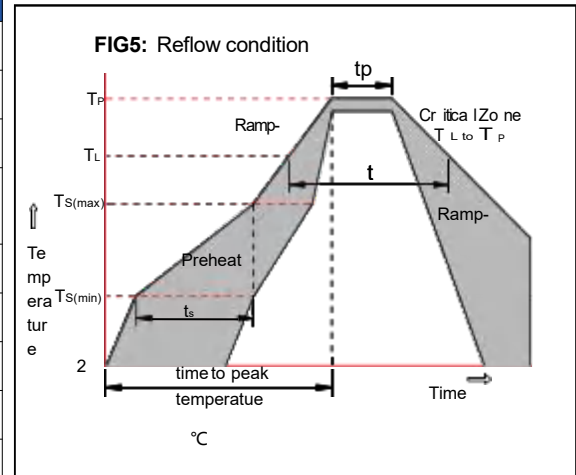


Fig.8 Gate Charge Waveform

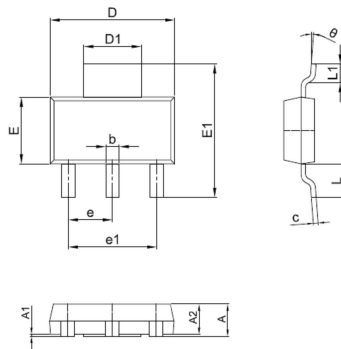
Soldering parameters

Reflow Condition		Pb-Free assembly (see as below)
Pre Heat	-Temperature Min ($T_{s(min)}$)	+150°C
	-Temperature Max($T_{s(max)}$)	+200°C
	-Time (Min to Max) (ts)	60-180 secs.
Average ramp up rate (Liquid us Temp (T_L) to peak)		3°C/sec. Max
$T_{s(max)}$ to T_L - Ramp-up Rate		3°C/sec. Max
Reflow	-Temperature(T_L)(Liquid us)	+217°C
	-Temperature(t_L)	60-150 secs.
Peak Temp (T_P)		+260(+0/-5)°C
Time within 5°C of actual Peak Temp (t_p)		30 secs. Max
Ramp-down Rate		6°C/sec. Max
Time 25°C to Peak Temp (T_P)		8 min. Max
Do not exceed		+260°C

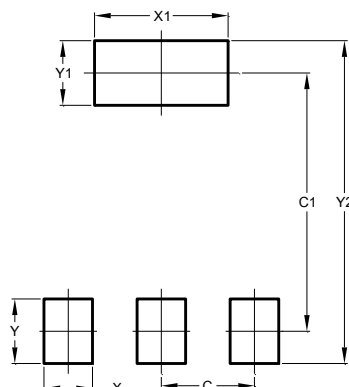


Package Dimensions & Suggested Pad Layout

SOT-223

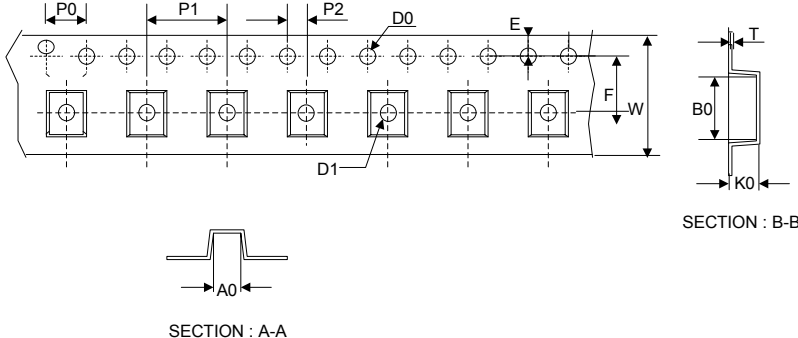
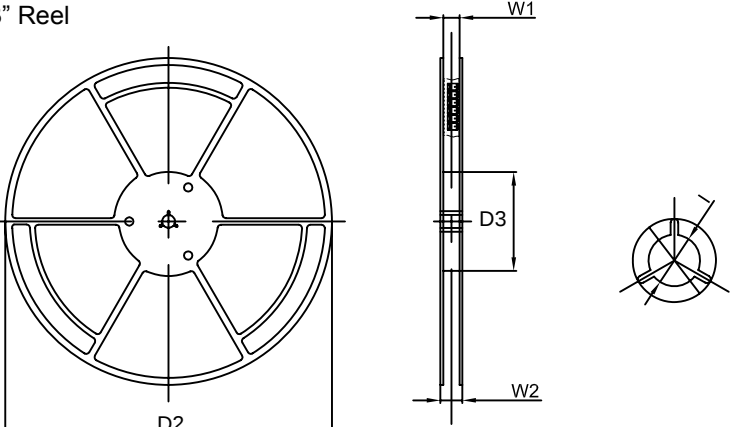


Symbol	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	1.50	1.80	0.059	0.071
A1	0.00	0.10	0.000	0.004
A2	1.50	1.70	0.059	0.067
b	0.65	0.75	0.026	0.030
c	0.20	0.30	0.008	0.012
D	6.40	6.60	0.252	0.260
D1	2.90	3.10	0.114	0.122
E	3.30	3.70	0.130	0.146
E1	6.85	7.15	0.270	0.281
e	2.20	2.40	0.087	0.094
e1	4.40	4.80	0.173	0.189
L	1.65	1.85	0.065	0.073
L1	0.90	1.15	0.035	0.045



Dimensions	Value (in mm)
C	2.30
C1	6.00
X	1.20
X1	3.60
Y	1.70
Y1	1.70
Y2	7.70

Tape & reel specification

Tape		Symbol	Dimension (mm)
		P0	4.00±0.20
		P1	8.00±0.20
		P2	2.00±0.20
		D0	1.55±0.20
		D1	1.55±0.20
		E	1.75±0.20
		F	5.50±0.20
		W	12.00±0.20
		A0	7.40±0.20
		B0	7.50±0.20
		K0	2.10±0.20
		T	0.20±0.20
		D2	330.0±5.0
		D3	100.0±4.0
13" Reel		Symbol	Dimension (mm)
		W1	18.0±5.0
		W2	22.0±5.0
		I	13.0±2.0
		Quantity: 2500PCS	